Amendments to the Specification

At page 1 before the "Technical Field" section, please insert the following:

--RELATED PATENT DATA

This patent resulted from a continuation application of U.S. Patent Application Serial No. 10/293,164, filed November 12, 2002, entitled "Methods of Masking and Etching a Semiconductor Substrate, and Ion Implant Lithography Methods of Processing a Semiconductor Substrate", naming J. Brett Rolfson as inventor, the disclosure of which is incorporated by reference; which patent resulted from a continuation application of U.S. Patent Application Serial No. 09/614,359, filed July 12, 2000, entitled "Methods of Masking and Etching a Semiconductor Substrate, and Ion Implant Lithography Methods of Processing a Semiconductor Substrate", naming J. Brett Rolfson as inventor, now U.S. Patent No. 6,486,074 B1, the disclosure of which is incorporated by reference.--

Please amend the paragraph beginning at line 3 on page 10 as follows:

The invention was primarily motivated in overcoming concerns associated with ion lithographic processing. However, the invention is also seen to be applicable to other energy processing of imaging layers, such as using photoprocessing with actinic energy. For example, suitable energy, time, filtering or structural patterning relative to a photoresist layer could be conducted to achieve the Fig. 2 or other construction. By way of example only, exemplary processing whereby less than an entirety of the thickness of a photoresist layer is processed is described with reference to our co-pending U.S. Patent Application Serial No. 09/444,280, filed on November 19, 1999, entitled "Microelectronic Device Fabricating Method, Integrated Circuit, and Intermediate Construction" listing Alan R. Reinberg as an inventor, and which is now U.S. Patent No. 6,232,229 B1, and which is hereby fully incorporated by reference.